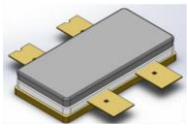
Gallium Nitride 50V, 200W,2.3-2.7GHz RF Power Transistor

Description

STBV27200B4C



The STBV27200B4C is a 200-watt, internally matched GaN HEMT, designed for 5G cellular applications with frequencies from 2.3-2.7GHz, **enabled by wide band VBW capability to support IBW up to 200MHz.**.

It can be configured as asymmetrical Doherty for 4G or 5G application, delivering 30W average power, according to normal 9dB back off.

There is no guarantee of performance when this part is used in applications designed Outside of these frequencies.

- Typical Doherty Pulsed CW and 1C W--CDMA Characterization Performance (Objective):

Freq (GHz)	Pulse CW Signal(1)				P_{avg}=45dBm WCDMA Signal(2)		
	P1 (dBm)	P1_Gain (dB)	P3 (dBm)	P3 (W)	Gp (dB)	η_D (%)	$ACPR_{5M}$ (dBc)
2.5-2.7	52	15	53.2	210	15	56	-30
2.3-2.4	52	15	53	200	15	59	-30

Applications

- Asymmetrical Doherty amplifier within N41 5G band and B41 4G band， B40 4G band
- S band power amplifier

Important Note: Proper Biasing Sequence for GaN HEMT Transistors

Turning the device ON

- 1. Set VGS to the pinch—off (VP) voltage, typically –5 V
- 2. Turn on VDS to nominal supply voltage
- 3. Increase VGS until IDS current is attained
- 4. Apply RF input power to desired level

Turning the device OFF

- 1. Turn RF power off
- 2. Reduce VGS down to VP, typically –5 V
- 3. Reduce VDS down to 0 V
- 4. Turn off VGS

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain--Source Voltage	V_{DSS}	+200	Vdc
Gate--Source Voltage	V_{GS}	-8 to +0.5	Vdc
Operating Voltage	V_{DD}	55	Vdc
Maximum gate current	Igs	27	mA
Storage Temperature Range	Tstg	-65 to +150	°C
Case Operating Temperature	T_C	+150	°C
Operating Junction Temperature	T_J	+225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case by FEA T_C= 85°C, Pout=30W,	$R_{\theta JC}$	2.2	°C /W

Table 3. Electrical Characteristics (TA = 25℃ unless otherwise noted)

DC Characteristics (main path, measured on wafer prior to packaging)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	VGS=-8V; IDS=10mA	V_{DSS}		200		V
Gate Threshold Voltage	VDS =10V, ID = 10mA	$V_{GS(th)}$	-4		-2	V
Gate Quiescent Voltage	VDS =50V, IDS=75mA, Measured in Functional Test	$V_{GS(Q)}$		-3		V

DC Characteristics (peak path, measured on wafer prior to packaging)

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit

Drain-Source Breakdown Voltage	VGS=-8V; IDS=17mA	V_{DSS}		200		V
Gate Threshold Voltage	VDS =10V, ID = 17mA	$V_{GS(th)}$	-4		-2	V
Gate Quiescent Voltage	VDS =50V, IDS=100mA, Measured in Functional Test	$V_{GS(Q)}$		-3		V

Ruggedness Characteristics

Characteristic	Conditions	Symbol	Min	Typ	Max	Unit
Load mismatch capability	2.6GHz, Pout=25W WCDMA 1 Carrier in Doherty circuit All phase, No device damages	VSWR		10:1		

2.5-2.7GHz

Typical RF performance

Figure 1：Gain，Eff as function of Pout under Pulsed CW condition

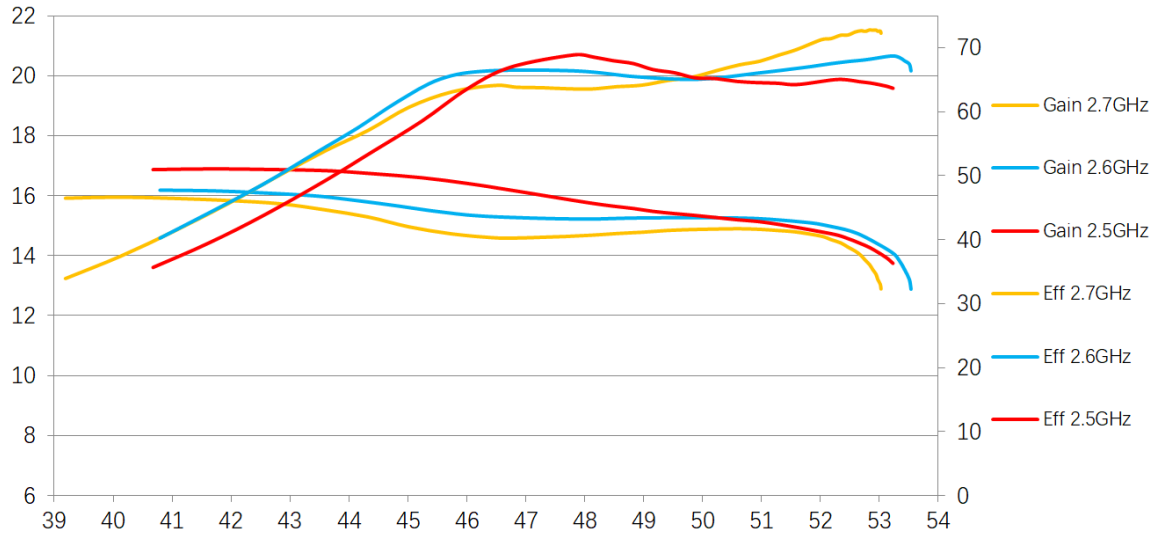


Figure 2: Network analyzer output, S11 S21 Curve Picture

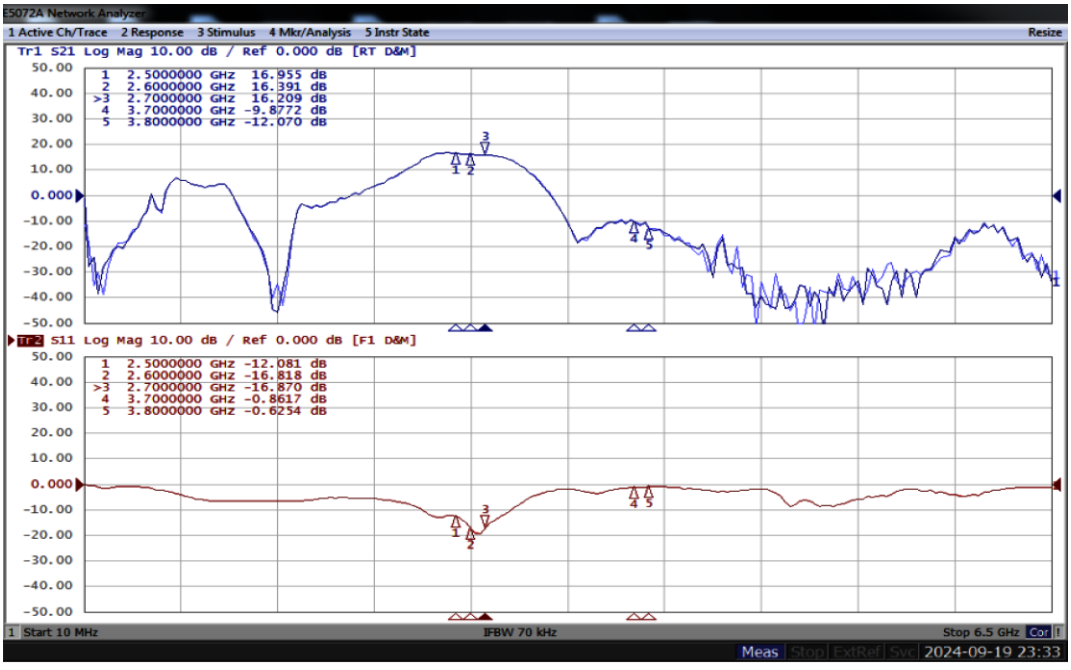
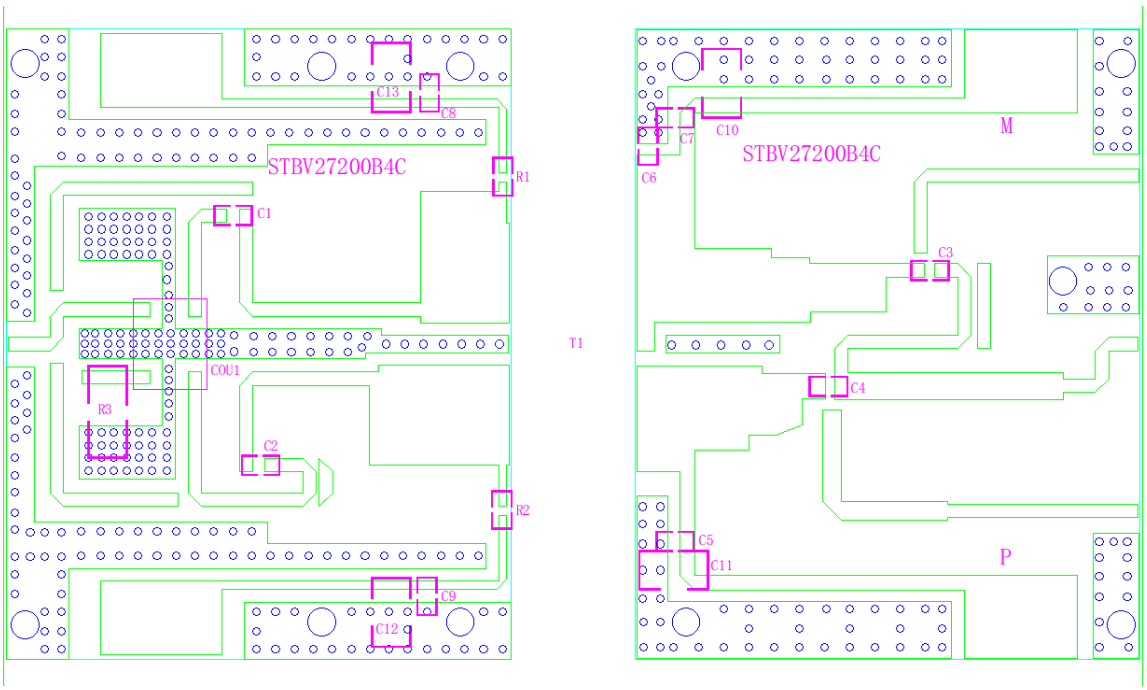


Figure 3: Picture of application board Doherty circuit



Test Board Bom				
Part	**Quantity**	**Description**	**Part Number**	**Manufacture**
C1,C2,C3 C4,C5,C7,C8,C9	8	10pFHigh Q Capacitor	251SHS100BSE	TEMEX
C6	1	0.5pFHigh Q Capacitor	251SHS0R5BSE	TEMEX
C10,C11,C12,C13	4	10uF MLCC	GRM32EC72A10	Murata
R1,R2	2	10Ω Power Resistor	ESR03EZPF100	ROHM
R3	1	51Ω Power Resistor	RFR50-20CT0421B	YT
COU1	1	3 dB Bridge	X3C26P1-03S	Anaren
T1	1	200W GaN Dual Transistor	STBV27200B4C	Innogration

2.3-2.4GHz

Typical RF performance

Figure 4：Gain，Eff as function of Pout under Pulsed CW condition

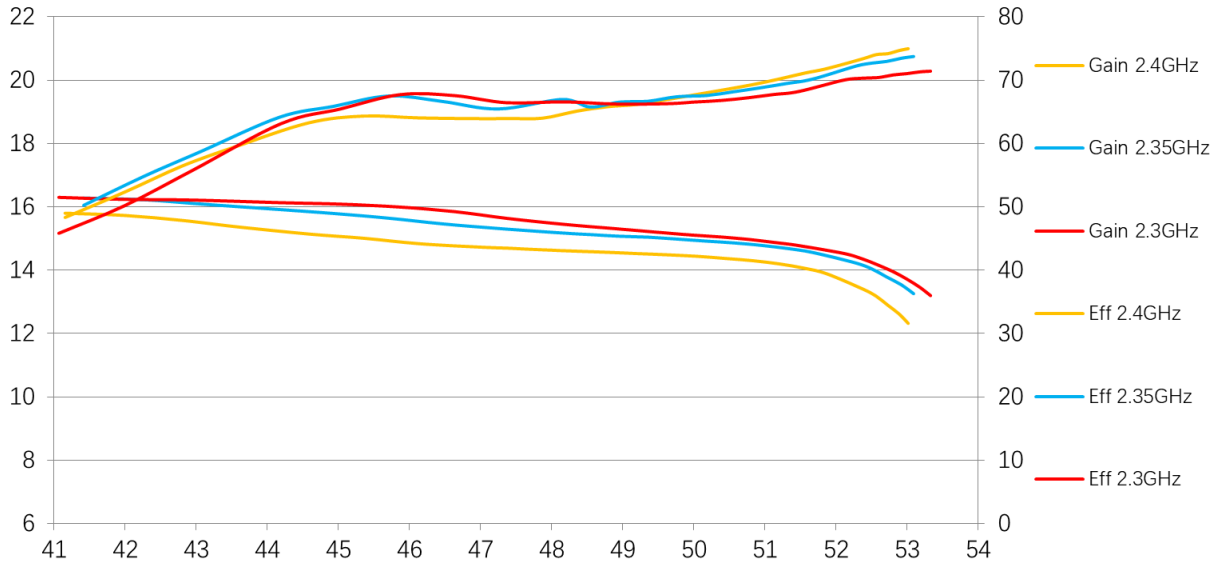


Figure 5: Network analyzer output, S11 S21 Curve Picture

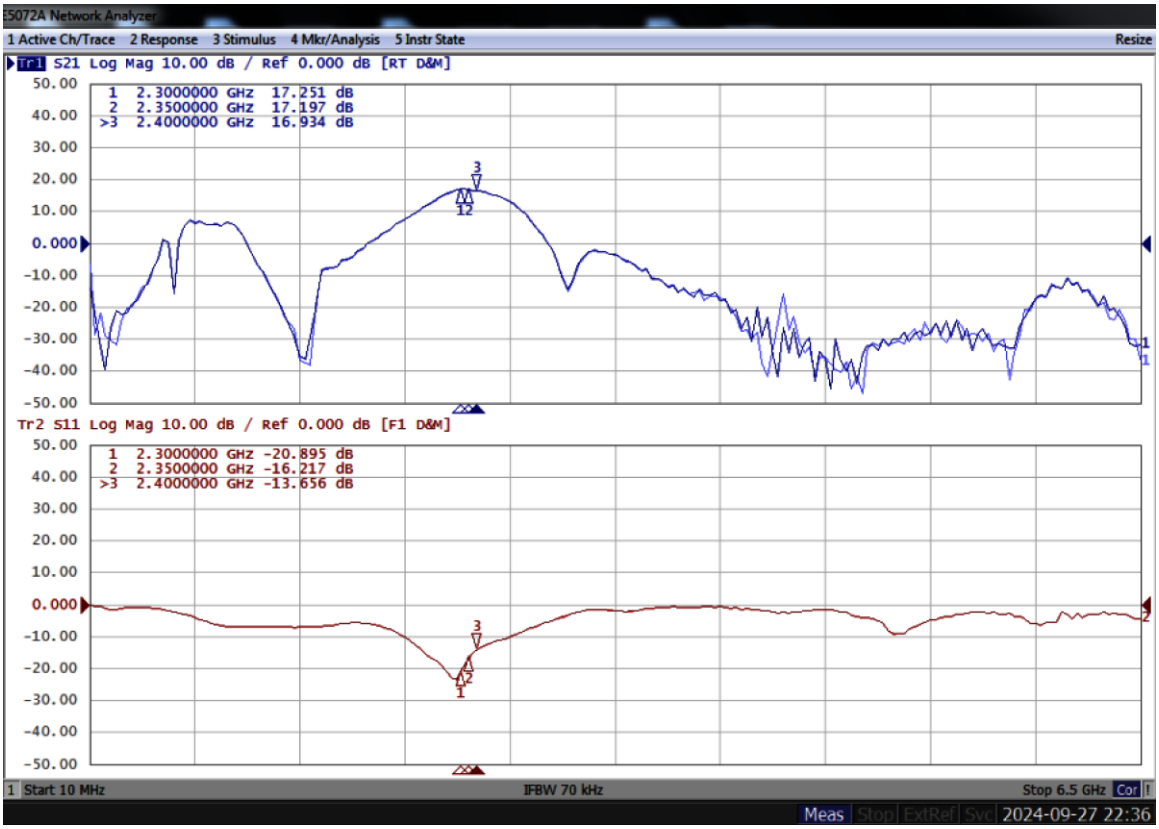
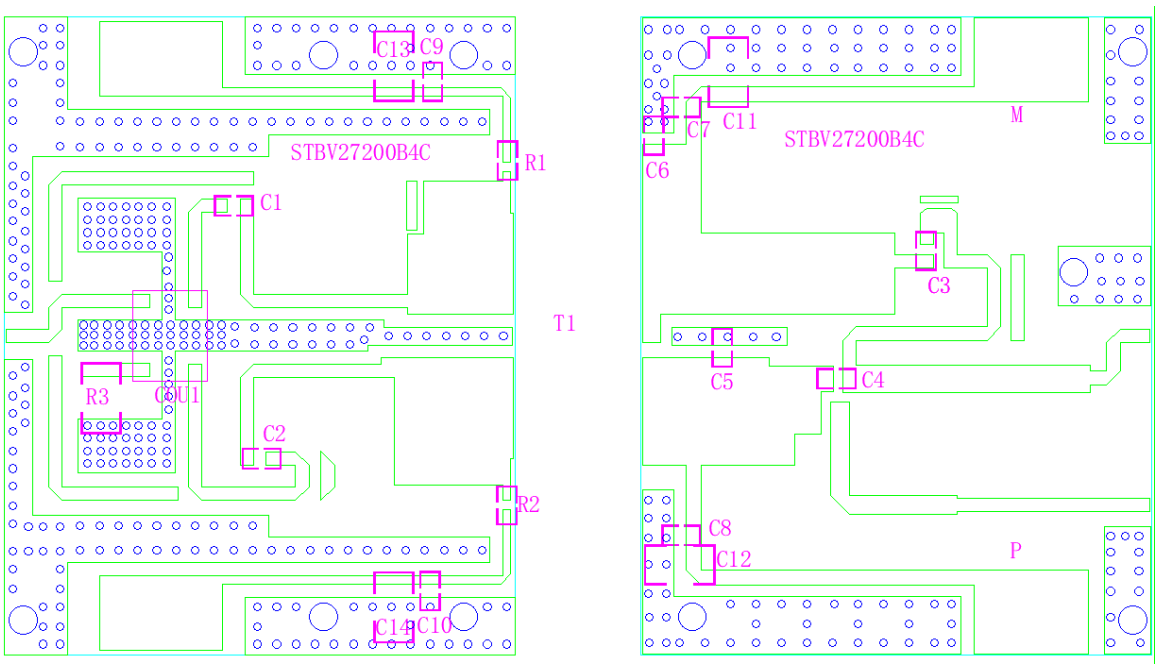


Figure 6: Picture of application board Doherty circuit



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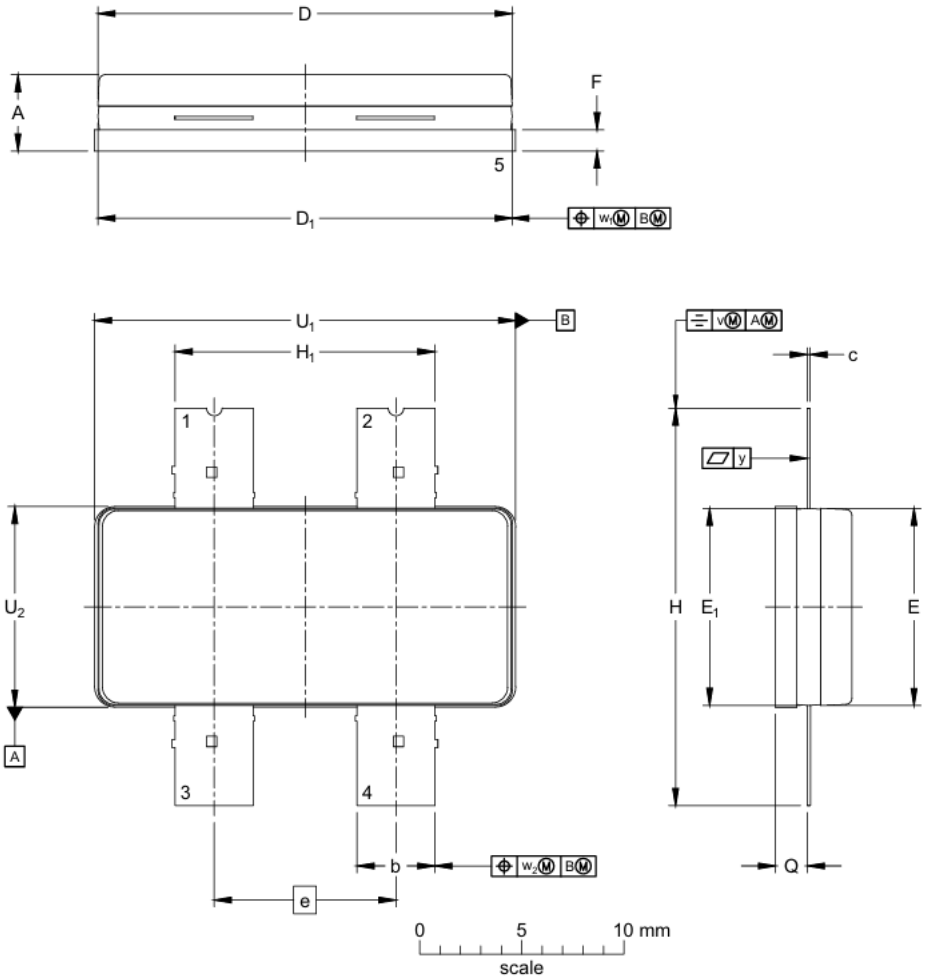
C6	1	0.7pFHigh Q Capacitor	251SHS0R7BSE	TEMEX
C5	1	1.0pFHigh Q Capacitor	251SHS1R0BSE	TEMEX
C11,C12,C13,C14	4	10uF MLCC	GRM32EC72A10	Murata
R1,R2	2	10Ω Power Resistor	ESR03EZPF100	ROHM
R3	1	51Ω Power Resistor	RFR50-20CT0421B	YT
COU1	1	3 dB Bridge	X3C26P1-03S	Anaren
T1	1	200W GaN Dual Transistor	STBV27200B4C	Innogration

Earless Flanged Plastic Air Cavity Package; 4 leads



Dimensions

Unit		A	b	c	D	D_1	E	E_1	e	F	H	H_1	Q(1)	U_1	U_2	v	w_1	w_2	y
mm	max	4.01	3.91	0.18	20.42	20.37	9.80	9.75		1.14	19.53	12.83	1.68	20.70	9.91	0.50	0.50	0.50	0.10
	nom								8.89										
	min	3.40	3.71	0.13	20.12	20.17	9.50	9.55		0.94	19.33	12.57	1.45	20.50	9.70				

Revision history

Table 4. Document revision history

Date	Revision	Datasheet Status
2024/10/8	**V1.0**	**Objective Datasheet Creation**
2024/10/24	**V1.1**	**Preliminary datasheet creation**

Application data based on LWH-24-35/36

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